

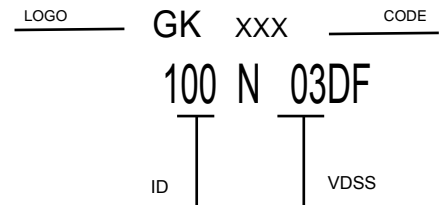
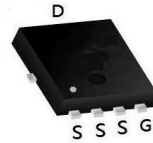
V_{DS} 30 V
 I_D 100 A
 $R_{DS(ON)}$ 3.3m Ω

Description

The 100N03DF is the high cell density trenched N-ch MOSFETs, which provide excellent R_{DS(ON)} and gate charge for most of the synchronous buck converter applications.

The 100N03DF meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

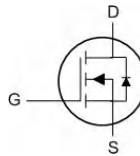
PDFN3x3



Features

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	500	V
V_{GS}	Gate-to-Source Voltage	± 30	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	5
		$T_C = 100^\circ\text{C}$	3
I_{DM}	Pulsed Drain Current ⁽¹⁾	20	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	137	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	83
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	33	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.5	
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	500	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±30V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 2.5A	-	1.40	1.81	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	615	-	pF
C _{oss}	Output Capacitance		-	67	-	pF
C _{rss}	Reverse Transfer Capacitance		-	10	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 250V, I _D = 2A	-	14	-	nC
Q _{gs}	Gate Source Charge		-	3.3	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	4	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 240V I _D = 2A, R _{GEN} = 24Ω	-	12	-	ns
t _r	Turn-On Rise Time		-	17	-	ns
t _{d(off)}	Turn-Off DelayTime		-	45	-	ns
t _f	Turn-Off Fall Time		-	25	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 5A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F = 5A, di/dt = 100A/us	-	340	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	2.9	-	μC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25ohm, L=10mH, I_{AS}=5.3A
 3. RθJA is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB
 4. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.

RATING AND CHARACTERISTIC CURVES

Figure 1: Output Characteristics

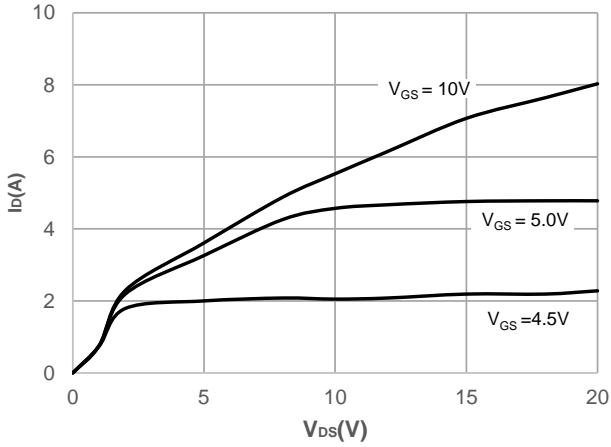


Figure 2: Typical Transfer Characteristics

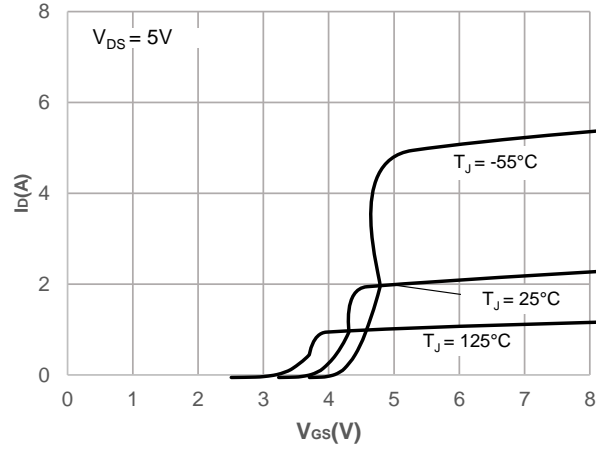


Figure 3: On-resistance vs. Drain Current

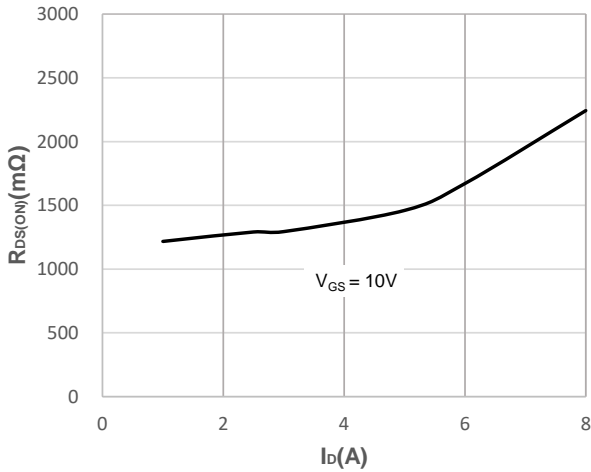


Figure 4: Body Diode Characteristics

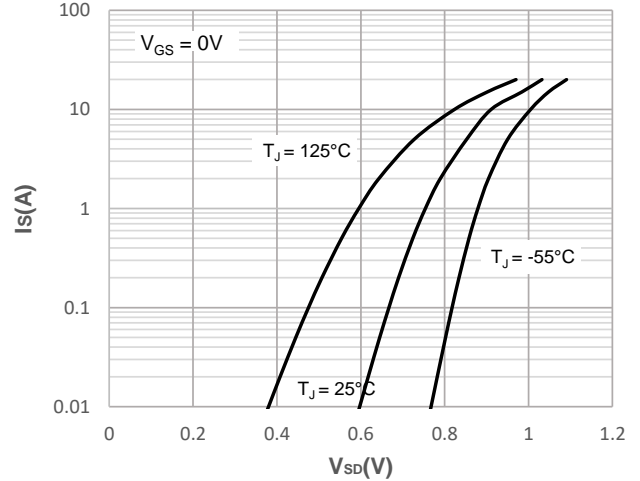


Figure 5: Gate Charge Characteristics

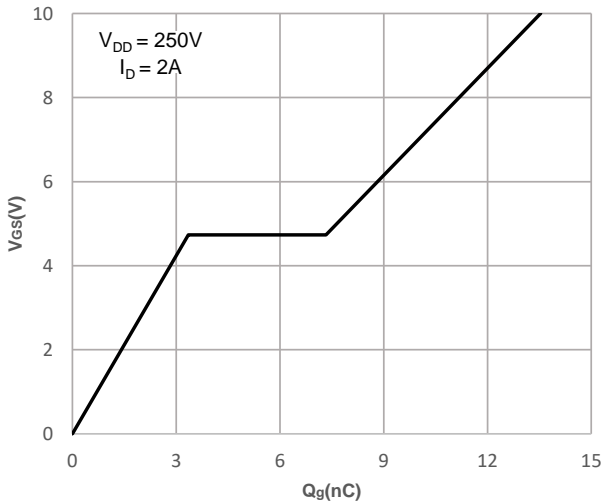
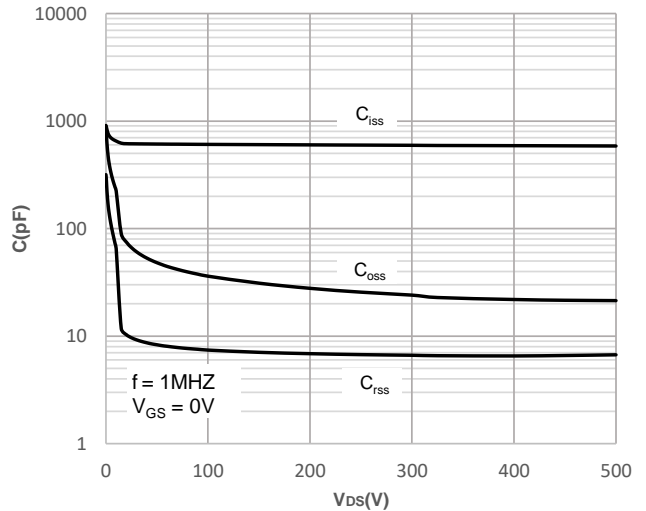


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

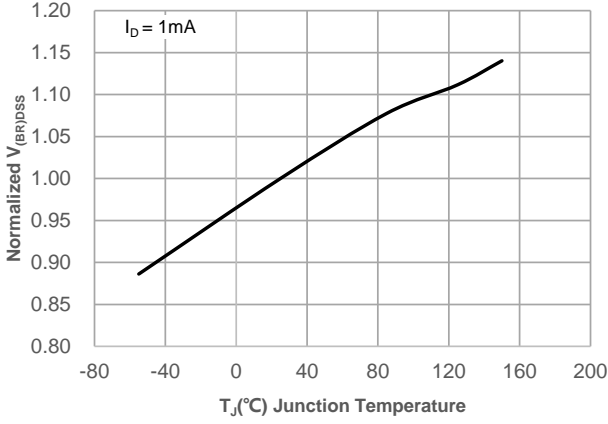


Figure 8: Normalized on Resistance vs. Junction Temperature

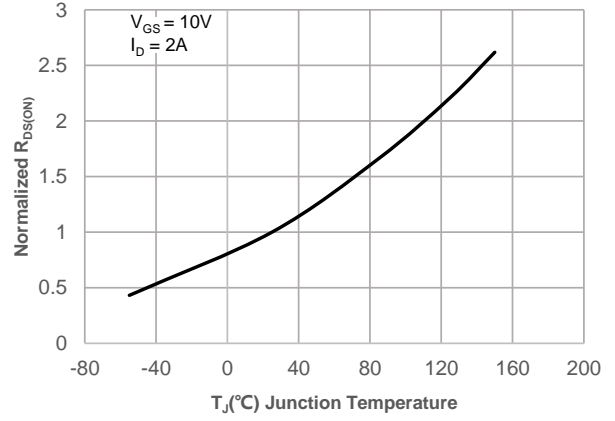


Figure 9: Maximum Safe Operating Area

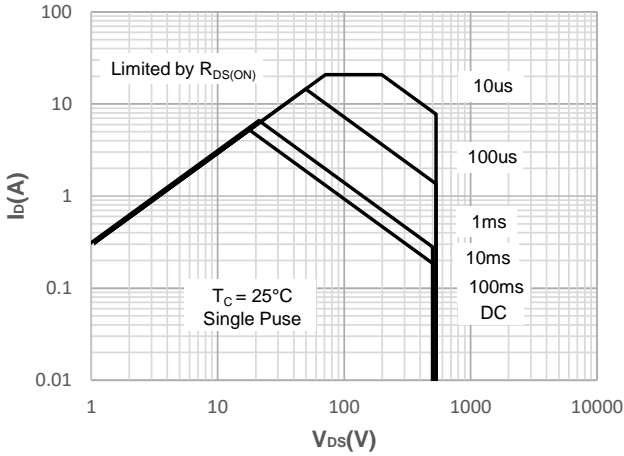


Figure 10: Maximum Continuous Driand Current vs. Case Temperature

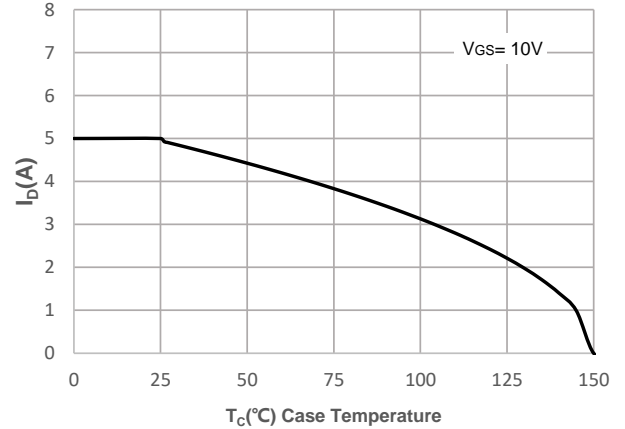


Figure 11: Normalized Maximum Transient Thermal Impedance

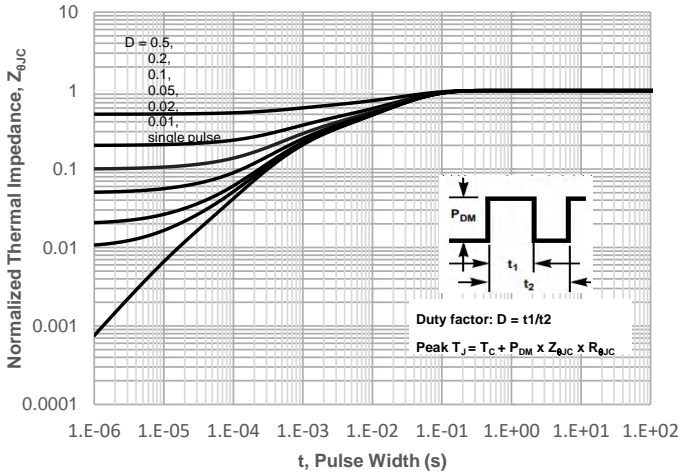
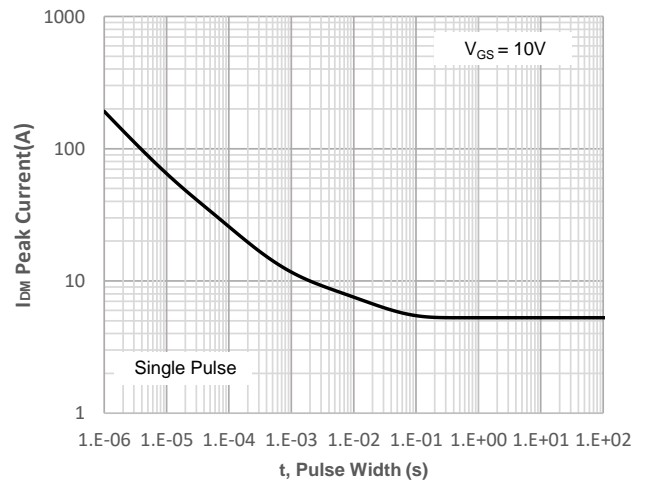
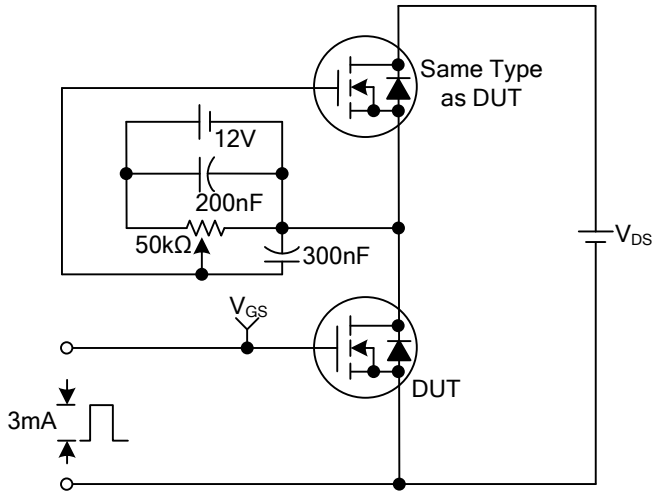


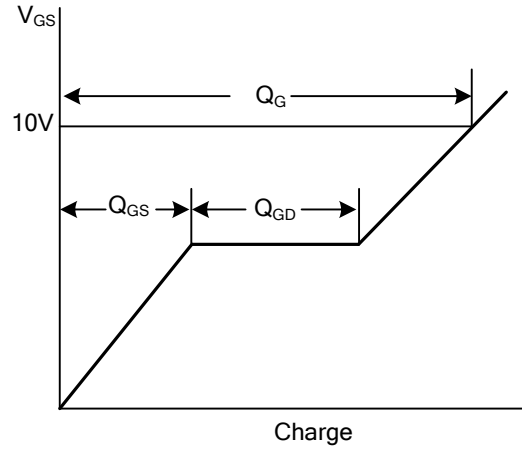
Figure 12: Peak Current Capacity



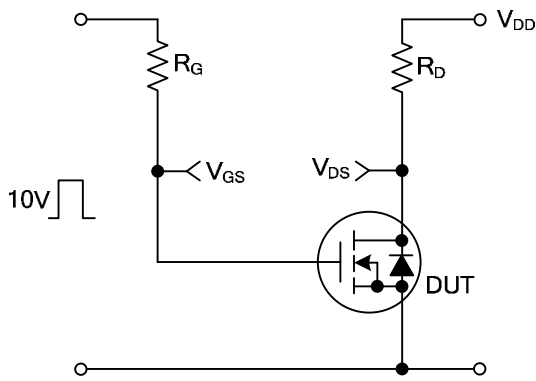
Test Circuit



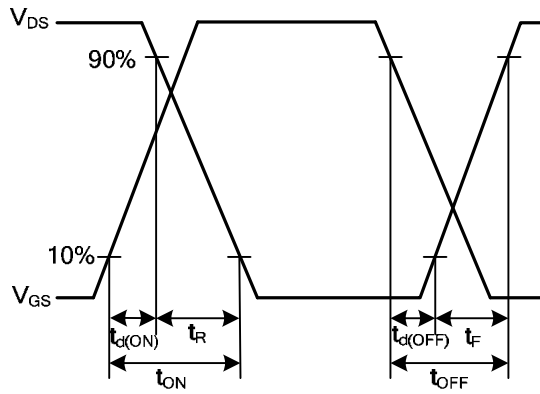
Gate Charge Test Circuit



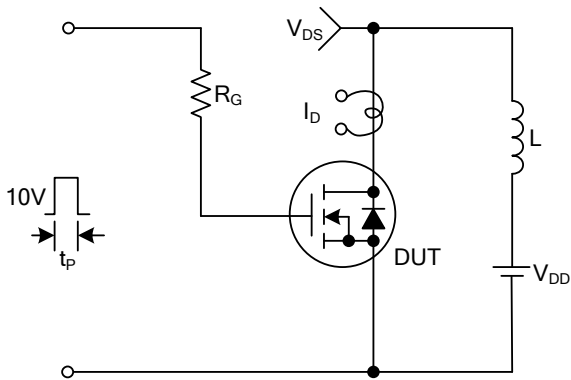
Gate Charge Waveforms



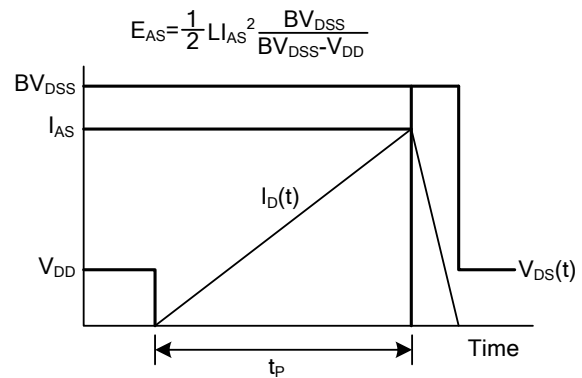
Resistive Switching Test Circuit



Resistive Switching Waveforms



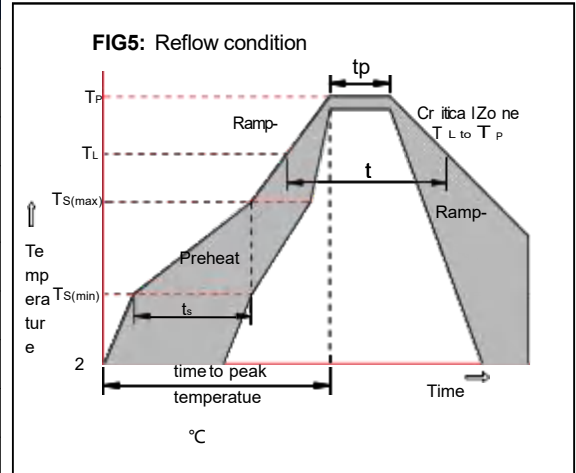
Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

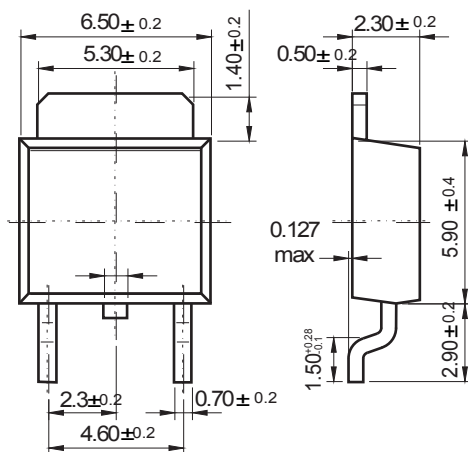
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max ($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature (T_L) (Liquid us)	+217 °C
	-Temperature (t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

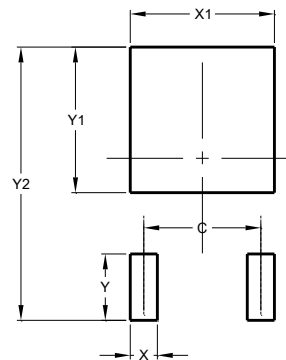


Package Dimensions & Suggested Pad Layout

TO-252



Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

Tape & reel specification

Tape		Symbol	Dimension (mm)
<p>SECTION : A-A</p> <p>SECTION : B-B</p>		P0	4.00±0.20
		P1	8.00±0.20
		P2	2.00±0.20
		D0	1.55±0.15
		D1	1.55±0.20
		E	1.75±0.20
		F	7.50±0.20
		W	16.00±0.20
		A0	7.10±0.20
		B0	10.50±0.20
		K0	2.70±0.20
		T	0.30±0.10
		D2	330.0±5.0
		D3	100.0±4.0
		W1	20.0±5.0
W2	25.0±5.0		
I	13.0±2.0		
		Quantity: 2500PCS	

